

# GP1S094HCZ0F

Gap : 3mm, Slit : 0.3mm  
Phototransistor Output,  
Compact Transmissive  
Photointerrupter



## ■ Description

**GP1S094HCZ0F** is a compact-package, phototransistor output, transmissive photointerrupter, with opposing emitter and detector in a molding that provides non-contact sensing. The compact package series is a result of unique technology combining transfer and injection molding.

This device has a wide gap and positioning pins.

## ■ Features

1. Transmissive with phototransistor output
2. Highlights:
  - Compact Size
  - Positioning Pin to prevent misalignment
3. Key Parameters:
  - Gap Width : 3mm
  - Slit Width (detector side): 0.3mm
  - Package : 5.5×2.6×4.8mm
4. RoHS directive compliant

## ■ Agency approvals/Compliance

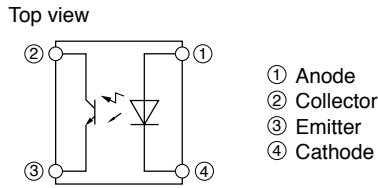
1. Compliant with RoHS directive

## ■ Applications

1. Detection of object presence or motion.
2. Example: printer, lens control for camera

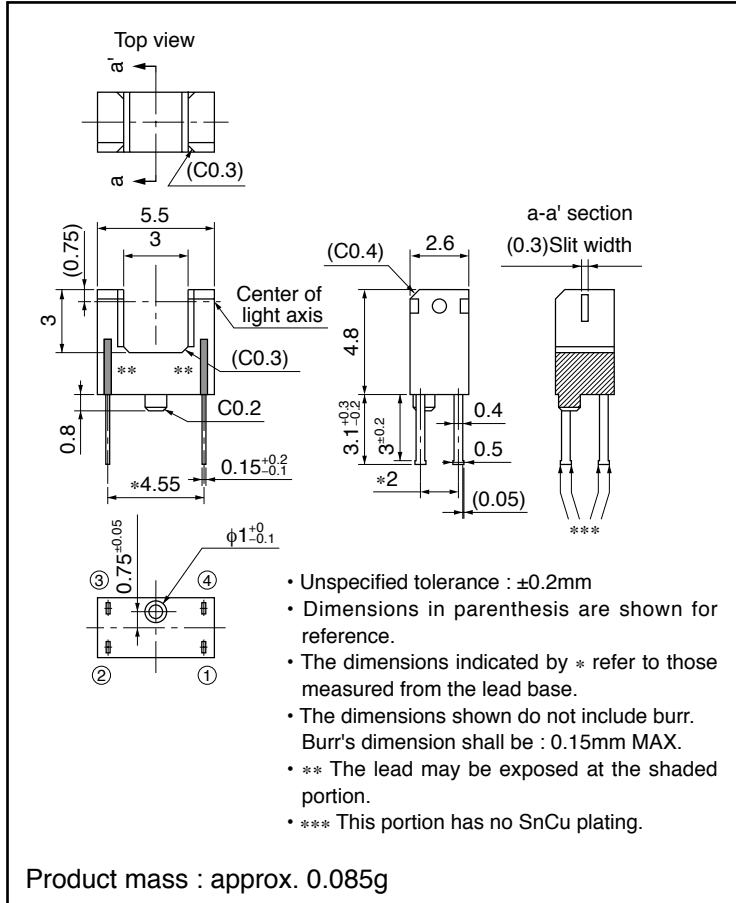
Notice The content of data sheet is subject to change without prior notice.  
In the absence of confirmation by device specification sheets, SHARP takes no responsibility for any defects that may occur in equipment using any SHARP devices shown in catalogs, data books, etc. Contact SHARP in order to obtain the latest device specification sheets before using any SHARP device.

## Internal Connection Diagram



## Outline Dimensions

(Unit : mm)



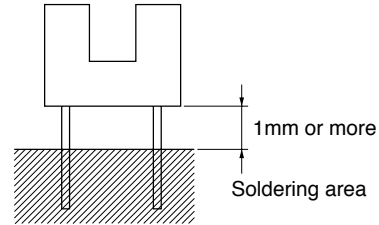
Plating material : SnCu (Cu : TYP. 2%)

Country of origin  
Japan

## ■ Absolute Maximum Ratings ( $T_a=25^{\circ}\text{C}$ )

Parameter		Symbol	Rating	Unit
Input	Forward current	$I_F$	50	mA
	Reverse voltage	$V_R$	6	V
	Power dissipation	P	75	mW
Output	Collector-emitter voltage	$V_{CEO}$	35	V
	Emitter-collector voltage	$V_{ECO}$	6	V
	Collector current	$I_C$	20	mA
	Collector power dissipation	$P_C$	75	mW
Total power dissipation		$P_{tot}$	100	mW
Operating temperature		$T_{opr}$	-25 to +85	$^{\circ}\text{C}$
Storage temperature		$T_{stg}$	-40 to +100	$^{\circ}\text{C}$
*1 Soldering temperature		$T_{sol}$	260	$^{\circ}\text{C}$

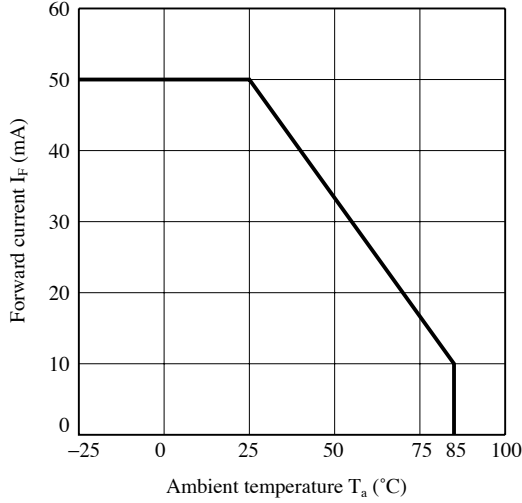
\*1 For 5s or less



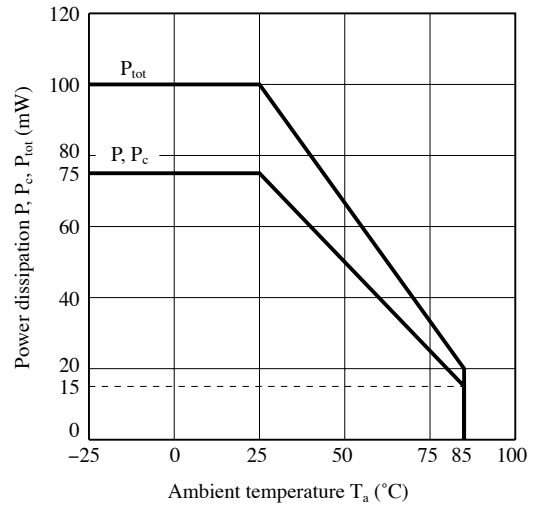
## ■ Electro-optical Characteristics ( $T_a=25^{\circ}\text{C}$ )

Parameter		Symbol	Condition	MIN.	TYP.	MAX.	Unit	
Input	Forward voltage	$V_F$	$I_F=20\text{mA}$	-	1.2	1.4	V	
	Reverse current	$I_R$	$V_R=3\text{V}$	-	-	10	$\mu\text{A}$	
Output	Collector dark current	$I_{CEO}$	$V_{CE}=20\text{V}$	-	-	100	nA	
Transfer characteristics	Collector current	$I_C$	$V_{CE}=5\text{V}, I_F=5\text{mA}$	40	-	400	$\mu\text{A}$	
	Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_F=10\text{mA}, I_C=40\mu\text{A}$	-	-	0.4	V	
	Response time	Rise time	$t_r$	$V_{CE}=5\text{V}, I_C=100\mu\text{A}, R_L=1\text{k}\Omega$	-	50	150	$\mu\text{s}$
		Fall time	$t_f$		-	50	150	$\mu\text{s}$

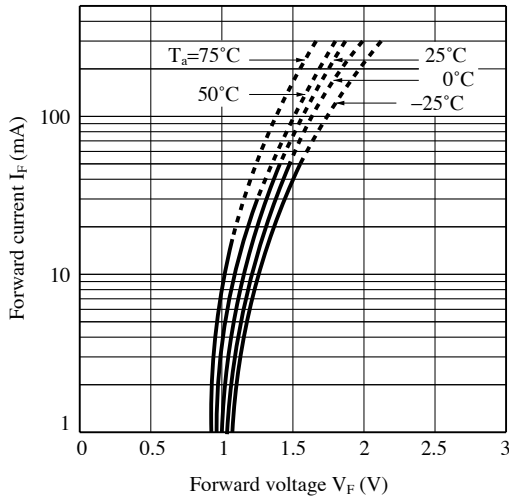
**Fig.1 Forward Current vs. Ambient Temperature**



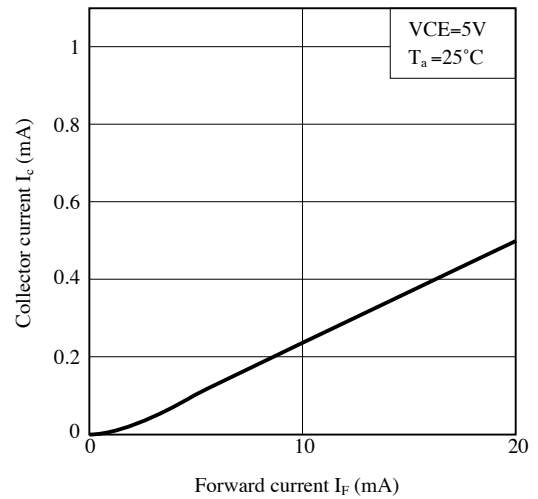
**Fig.2 Power Dissipation vs. Ambient Temperature**



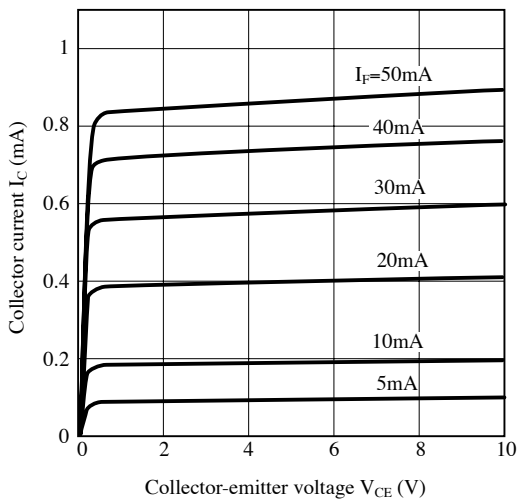
**Fig.3 Forward Current vs. Forward Voltage**



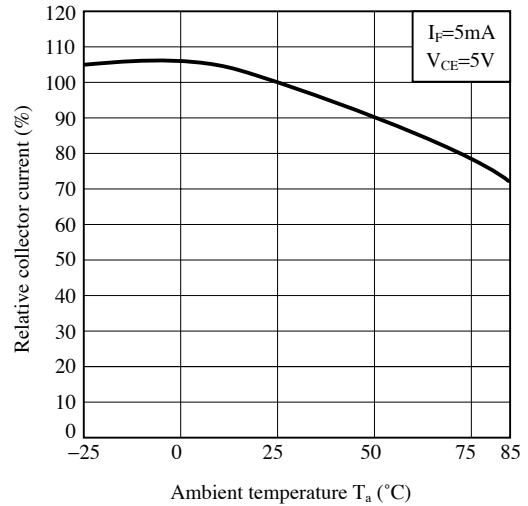
**Fig.4 Collector Current vs. Forward Current**



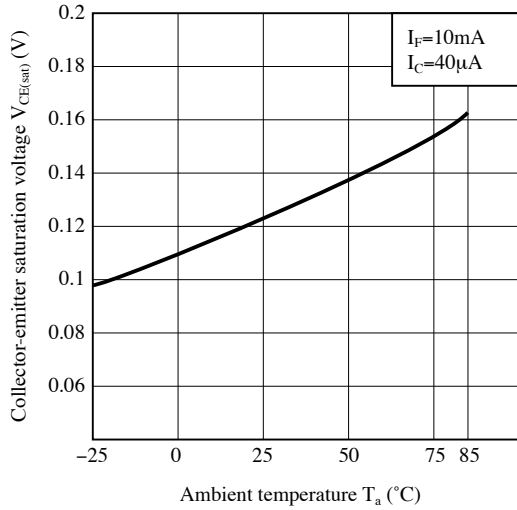
**Fig.5 Collector Current vs. Collector-emitter Voltage**



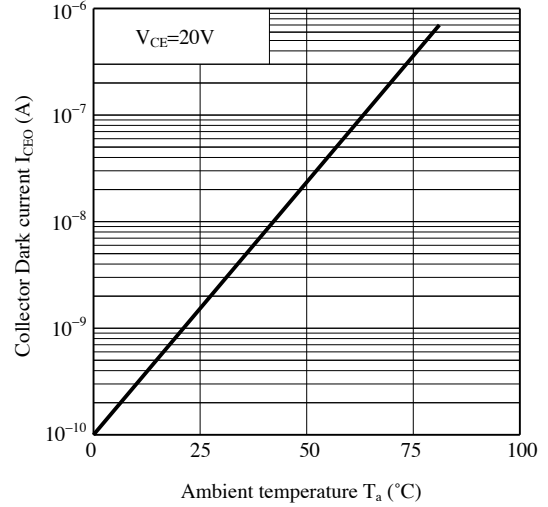
**Fig.6 Relative Collector Current vs. Ambient Temperature**



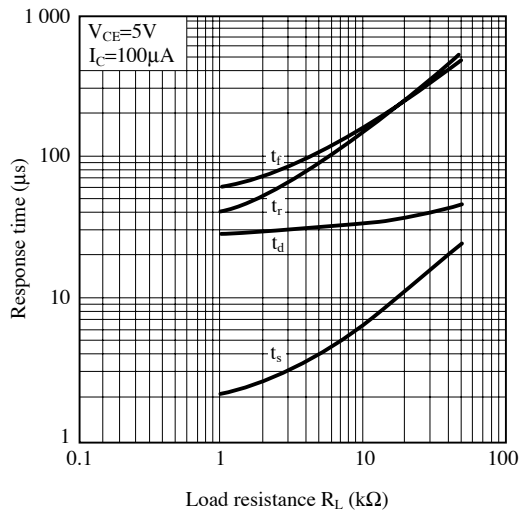
**Fig.7 Collector-emitter Saturation Voltage vs. Ambient Temperature**



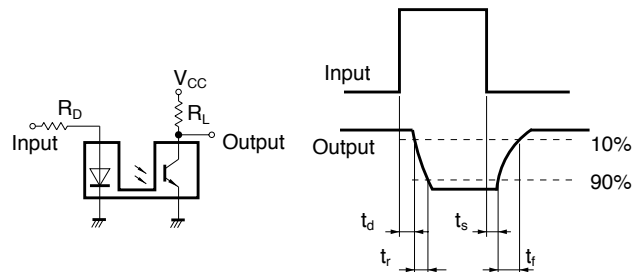
**Fig.8 Collector Dark Current vs. Ambient Temperature**



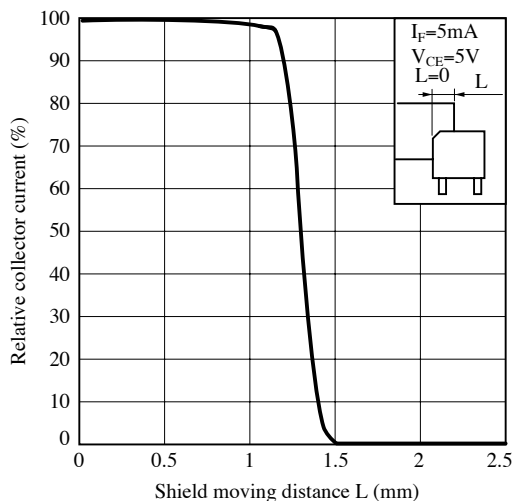
**Fig.9 Response Time vs. Load Resistance**



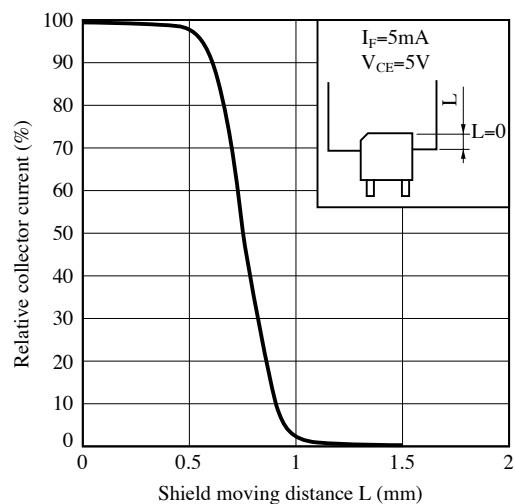
**Fig.10 Test Circuit for Response Time**



**Fig.11 Detecting Position Characteristics (1)**



**Fig.12 Detecting Position Characteristics (2)**



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.

■ **Design Considerations**

● **Design guide**

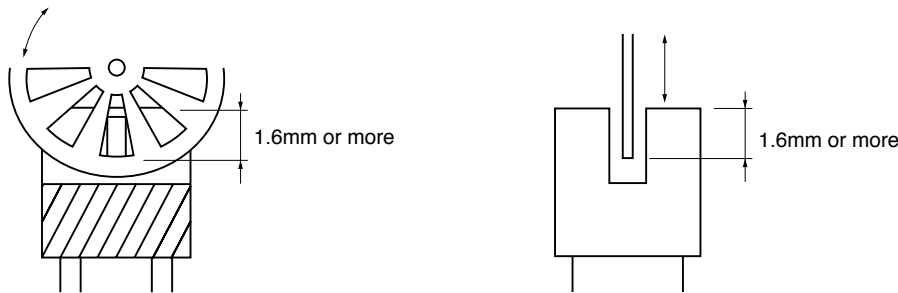
1) Prevention of detection error

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

2) Position of opaque board

Opaque board shall be installed at place 1.6mm or more from the top of elements.

(Example)



This product is not designed against irradiation and incorporates non-coherent IRED.

● **Degradation**

In general, the emission of the IRED used in photointerrupter will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

● **Parts**

This product is assembled using the below parts.

• **Photodetector (qty. : 1)**

Category	Material	Maximum Sensitivity wavelength (nm)	Sensitivity wavelength (nm)	Response time (μs)
Phototransistor	Silicon (Si)	930	700 to 1 200	20

• **Photo emitter (qty. : 1)**

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3

• **Material**

Case	Lead frame	Lead frame plating
Black polyphernylene sulfide resin (UL94 V-0)	42Alloy	SnCu plating

**■ Manufacturing Guidelines****● Soldering Method**

## Flow Soldering:

Soldering should be completed below 260°C and within 5 s.

Please solder within one time.

Soldering area is 1mm or more away from the bottom of housing.

Please take care not to let any external force exert on lead pins.

Please don't do soldering with preheating, and please don't do soldering by reflow.

## Hand soldering

Hand soldering should be completed within 3 s when the point of solder iron is below 350°C.

Please solder within one time.

Please don't touch the terminals directly by soldering iron.

Soldered product shall treat at normal temperature.

## Other notice

Please take care not to let any external force exert on lead pins.

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the cooling and soldering conditions.

**● Cleaning instructions**

## Solvent cleaning :

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

## Ultrasonic cleaning :

Do not execute ultrasonic cleaning.

## Recommended solvent materials :

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

**● Presence of ODC**

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).

**■ Package specification****● Sleeve package**

## Package materials

Sleeve : Polyphernylene

Stopper : Styrene-Elastomer

## Package method

MAX. 100 pcs. of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

MAX. 50 sleeves in one case.